

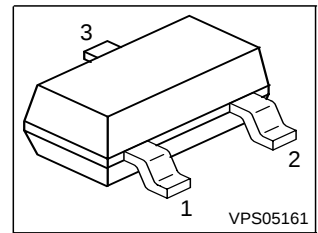
SIPMOS® Small-Signal-Transistor

Features

- P-Channel
- Enhancement mode
- Avalanche rated
- Logic Level
- dv/dt rated
- Pb-free lead plating; RoHS compliant

Product Summary

Drain source voltage	V_{DS}	-60	V
Drain-source on-state resistance	$R_{DS(on)}$	2	Ω
Continuous drain current	I_D	-0.33	A



Type	Package	Tape and Reel	Marking	Pin 1	PIN 2	PIN 3
BSS 83 P	PG-SOT-23	L6327: 3000pcs/r.	YAs	G	S	D

Maximum Ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current $T_A = 25\text{ °C}$ $T_A = 70\text{ °C}$	I_D	-0.33 -0.27	A
Pulsed drain current $T_A = 25\text{ °C}$	$I_{D\text{ puls}}$	-1.32	
Avalanche energy, single pulse $I_D = -0.33\text{ A}$, $V_{DD} = -25\text{ V}$, $R_{GS} = 25\text{ }\Omega$	E_{AS}	9.5	mJ
Avalanche energy, periodic limited by T_{jmax}	E_{AR}	0.036	
Reverse diode dv/dt $I_S = -0.33\text{ A}$, $V_{DS} = -48\text{ V}$, $di/dt = 200\text{ A}/\mu\text{s}$, $T_{jmax} = 150\text{ °C}$	dv/dt	6	kV/ μs
Gate source voltage	V_{GS}	± 20	V
Power dissipation $T_A = 25\text{ °C}$	P_{tot}	0.36	W
Operating and storage temperature	T_j , T_{stg}	-55...+150	$^{\circ}\text{C}$
IEC climatic category; DIN IEC 68-1		55/150/56	

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - soldering point (Pin 3)	R_{thJS}	-	-	150	K/W
SMD version, device on PCB:	R_{thJA}				
@ min. footprint		-	-	350	
@ 6 cm ² cooling area ¹⁾		-	-	300	

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain- source breakdown voltage $V_{GS} = 0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$	$V_{(BR)DSS}$	-60	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = -80\text{ }\mu\text{A}$	$V_{GS(th)}$	-1	-1.5	-2	
Zero gate voltage drain current $V_{DS} = -60\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$ $V_{DS} = -60\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 125\text{ }^\circ\text{C}$	I_{DSS}	-	-0.1 -10	-1 -100	μA
Gate-source leakage current $V_{GS} = -20\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	-	-10	-100	
Drain-source on-state resistance $V_{GS} = -4.5\text{ V}$, $I_D = -0.27\text{ A}$	$R_{DS(on)}$	-	2	3	Ω
Drain-source on-state resistance $V_{GS} = -10\text{ V}$, $I_D = -0.33\text{ A}$	$R_{DS(on)}$	-	1.4	2	

¹Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Transconductance $V_{DS} \geq 2 \cdot I_D \cdot R_{DS(ON)max}$, $I_D = -0.27\text{ A}$	g_{fs}	0.24	0.47	-	S
Input capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = -25\text{ V}$, $f = 1\text{ MHz}$	C_{iss}	-	62	78	pF
Output capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = -25\text{ V}$, $f = 1\text{ MHz}$	C_{oss}	-	19	24	
Reverse transfer capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = -25\text{ V}$, $f = 1\text{ MHz}$	C_{rss}	-	7	9	
Turn-on delay time $V_{DD} = -30\text{ V}$, $V_{GS} = -4.5\text{ V}$, $I_D = -0.27\text{ A}$, $R_G = 43\text{ }\Omega$	$t_{d(ON)}$	-	23	35	ns
Rise time $V_{DD} = -30\text{ V}$, $V_{GS} = -4.5\text{ V}$, $I_D = -0.27\text{ A}$, $R_G = 43\text{ }\Omega$	t_r	-	71	106	
Turn-off delay time $V_{DD} = -30\text{ V}$, $V_{GS} = -4.5\text{ V}$, $I_D = -0.27\text{ A}$, $R_G = 43\text{ }\Omega$	$t_{d(OFF)}$	-	56	70	
Fall time $V_{DD} = -30\text{ V}$, $V_{GS} = -4.5\text{ V}$, $I_D = -0.27\text{ A}$, $R_G = 43\text{ }\Omega$	t_f	-	61	76	

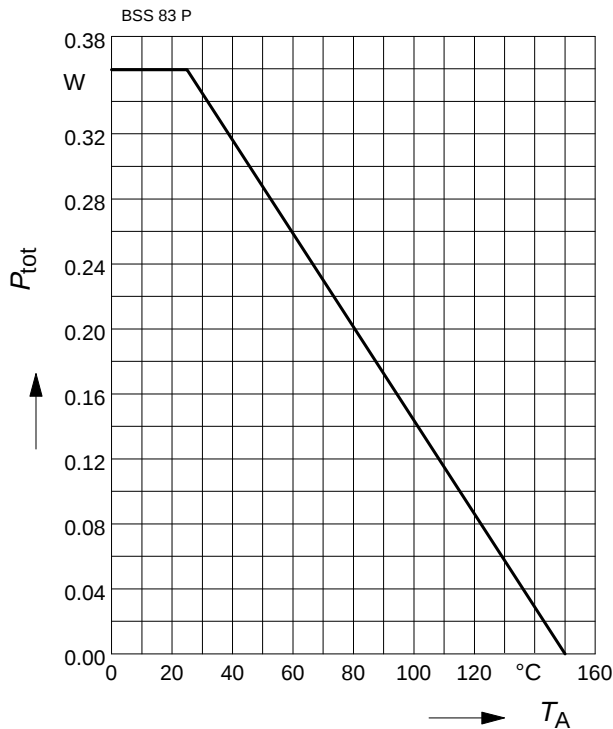
Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Gate to source charge $V_{DD} = -48\text{ V}$, $I_D = -0.33\text{ A}$	Q_{gs}	-	0.12	0.18	nC
Gate to drain charge $V_{DD} = -48$, $I_D = -0.33\text{ A}$	Q_{gd}	-	1.1	1.65	
Gate charge total $V_{DD} = -48\text{ V}$, $I_D = -0.33\text{ A}$, $V_{GS} = 0\text{ to }-10\text{ V}$	Q_g	-	2.38	3.57	
Gate plateau voltage $V_{DD} = -48\text{ V}$, $I_D = -0.33\text{ A}$	$V_{(\text{plateau})}$	-	-2.94	-	V

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Reverse Diode					
Inverse diode continuous forward current $T_A = 25\text{ }^{\circ}\text{C}$	I_S	-	-	-0.33	A
Inverse diode direct current,pulsed $T_A = 25\text{ }^{\circ}\text{C}$	I_{SM}	-	-	-1.32	
Inverse diode forward voltage $V_{GS} = 0\text{ V}$, $I_F = -0.33$	V_{SD}	-	-0.84	-1.1	V
Reverse recovery time $V_R = -30\text{ V}$, $I_F = I_S$, $di_F/dt = 80\text{ A}/\mu\text{s}$	t_{rr}	-	59.4	89	ns
Reverse recovery charge $V_R = -30\text{ V}$, $I_F = I_S$, $di_F/dt = 80\text{ A}/\mu\text{s}$	Q_{rr}	-	37.5	56	nC

Power Dissipation

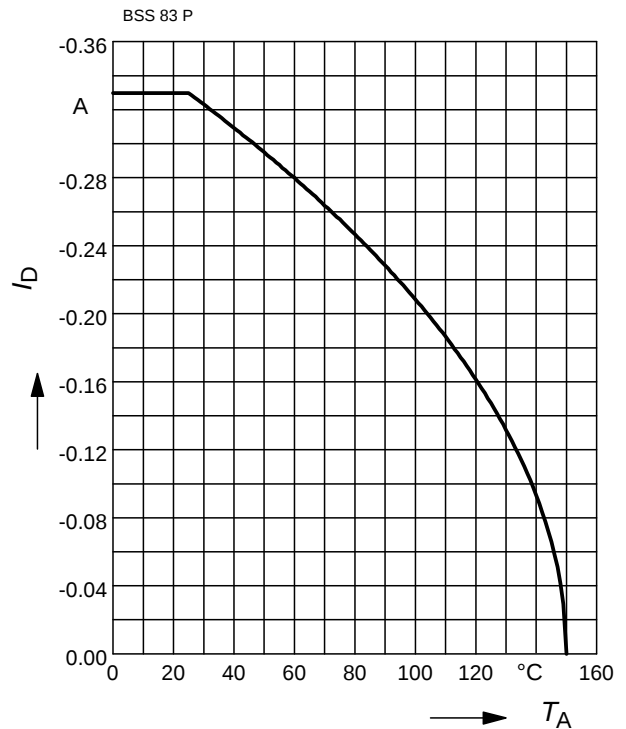
$$P_{\text{tot}} = f(T_A)$$



Drain current

$$I_D = f(T_A)$$

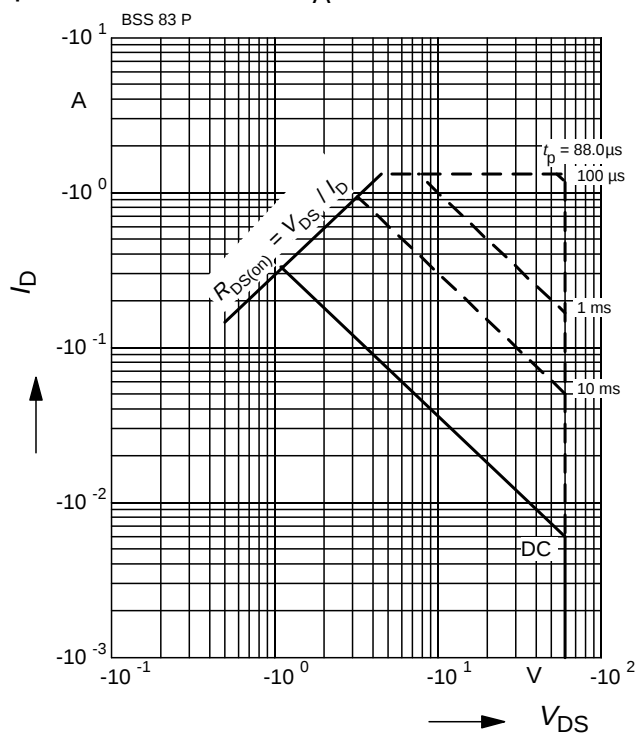
parameter: $V_{GS} \geq 10 \text{ V}$



Safe operating area

$$I_D = f(V_{DS})$$

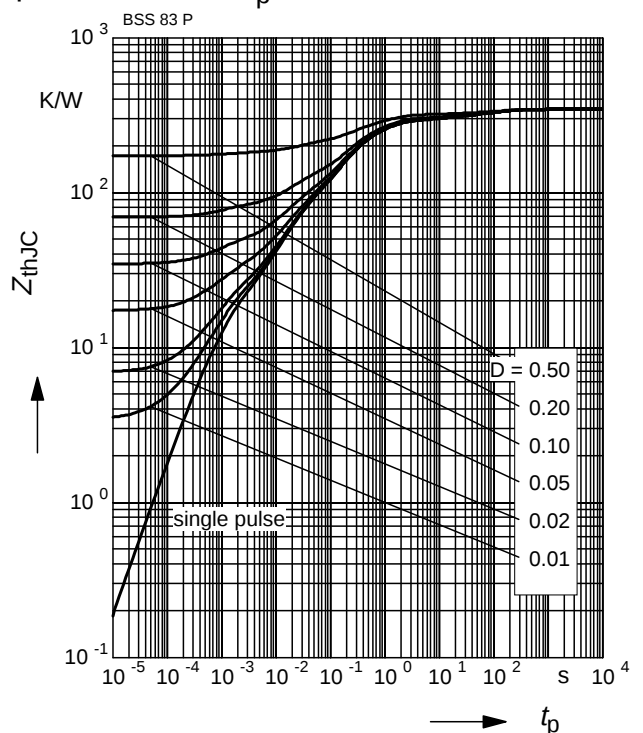
parameter: $D = 0$, $T_A = 25^\circ\text{C}$



Transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

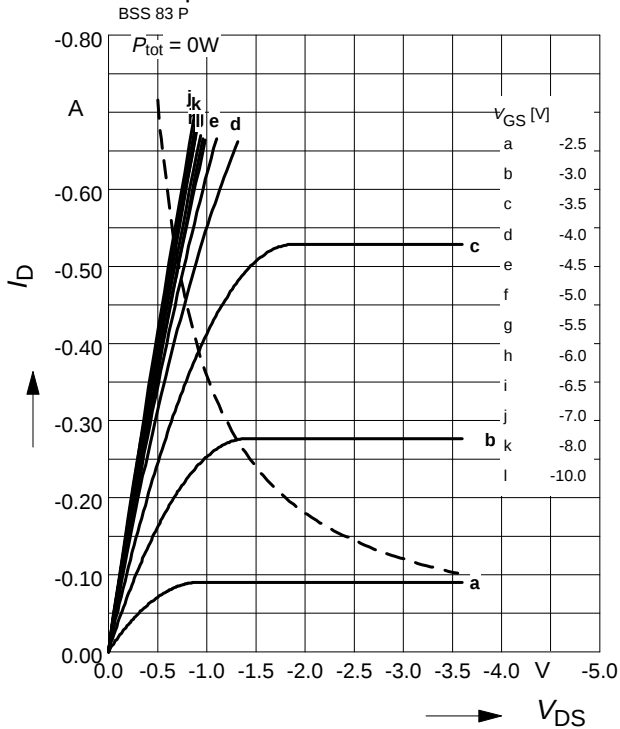
parameter: $D = t_p/T$



Typ. output characteristic

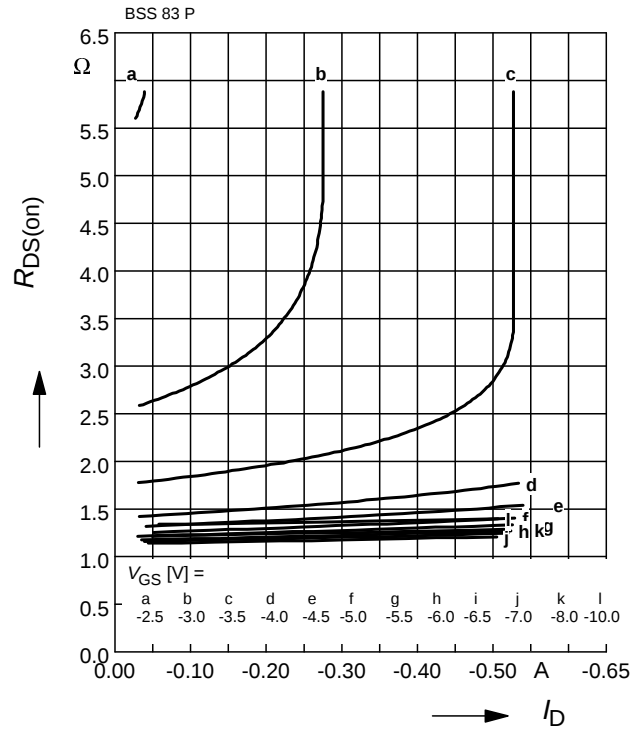
$$I_D = f(V_{DS}); T_J = 25^\circ\text{C}$$

parameter: $t_p = 80 \mu\text{s}$


Typ. drain-source-on-resistance

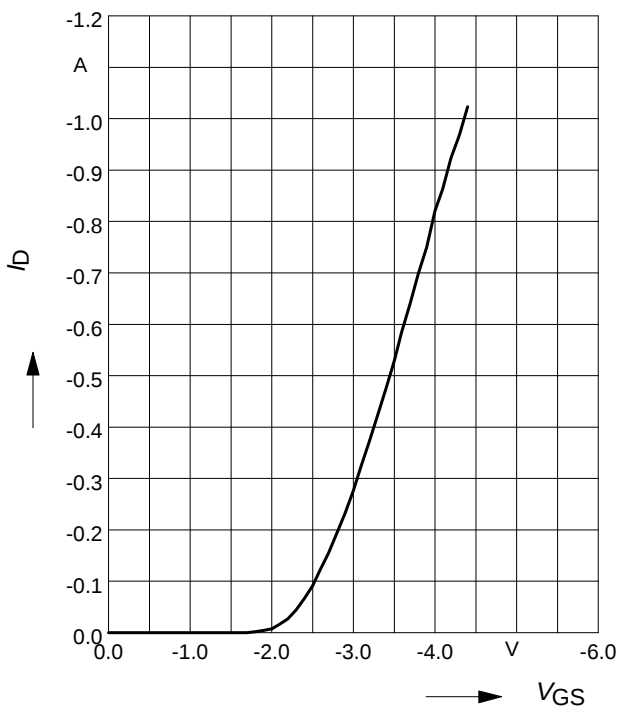
$$R_{DS(on)} = f(I_D)$$

parameter: V_{GS}


Typ. transfer characteristics $I_D = f(V_{GS})$

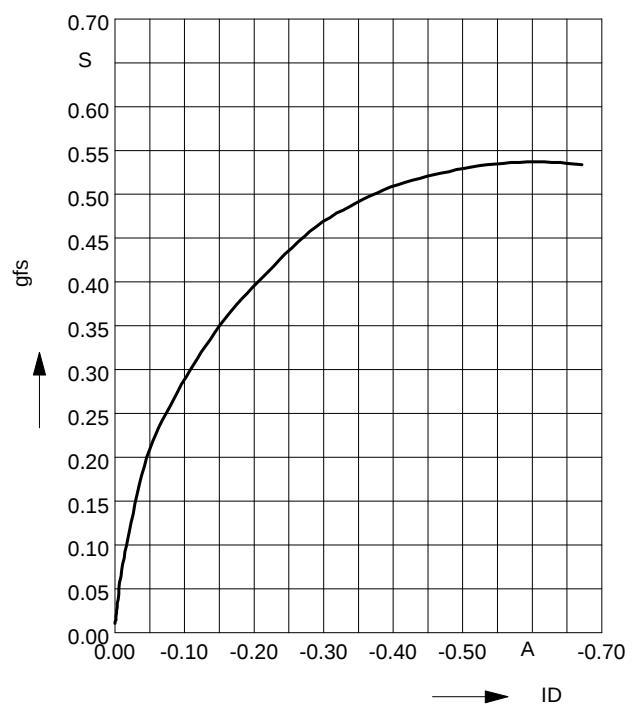
$$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

parameter: $t_p = 80 \mu\text{s}$


Typ. forward transconductance

$$g_{fs} = f(I_D); T_J = 25^\circ\text{C}$$

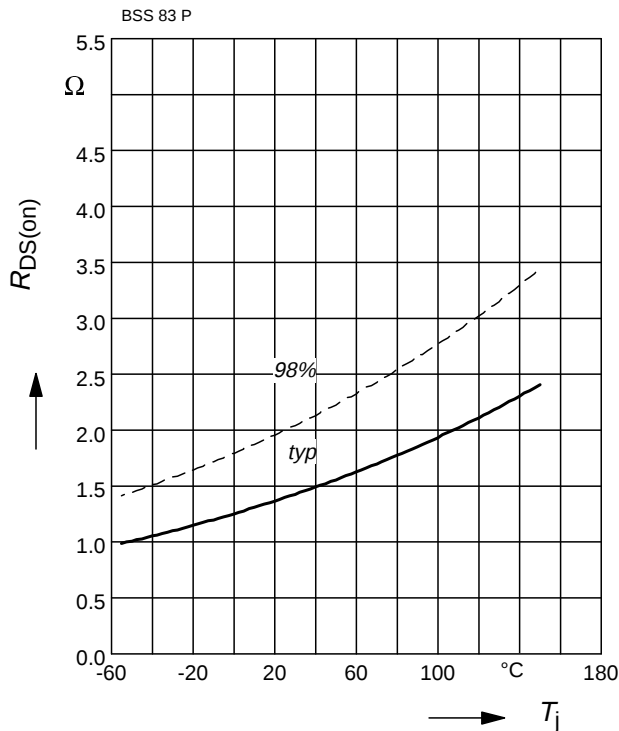
parameter: g_{fs}



Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

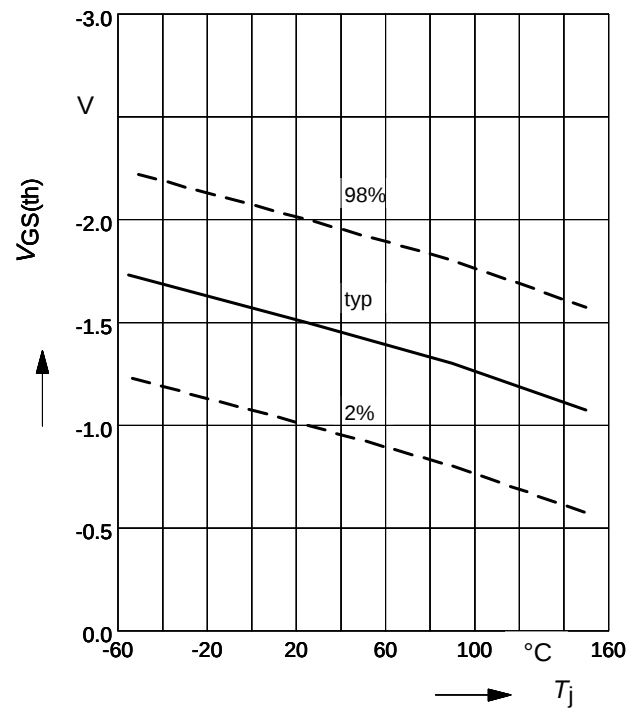
parameter: $I_D = -0.33 \text{ A}$, $V_{GS} = -10 \text{ V}$



Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

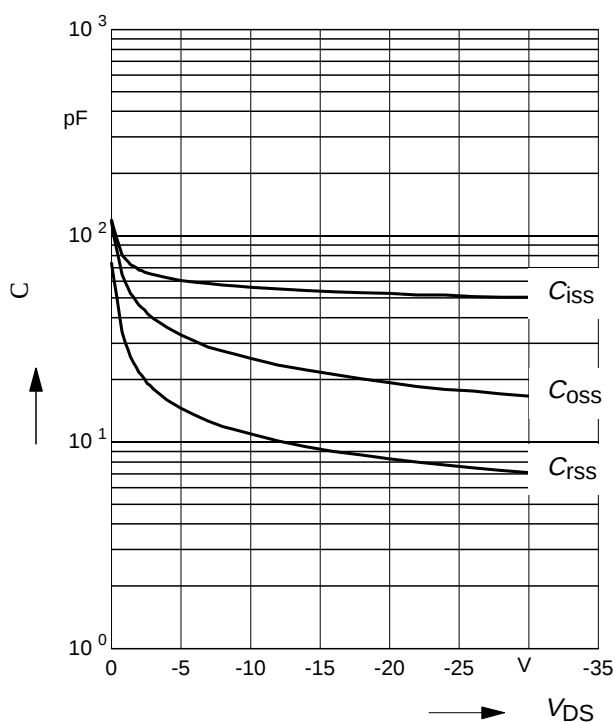
parameter: $V_{GS} = V_{DS}$, $I_D = -80 \mu\text{A}$



Typ. capacitances

$$C = f(V_{DS})$$

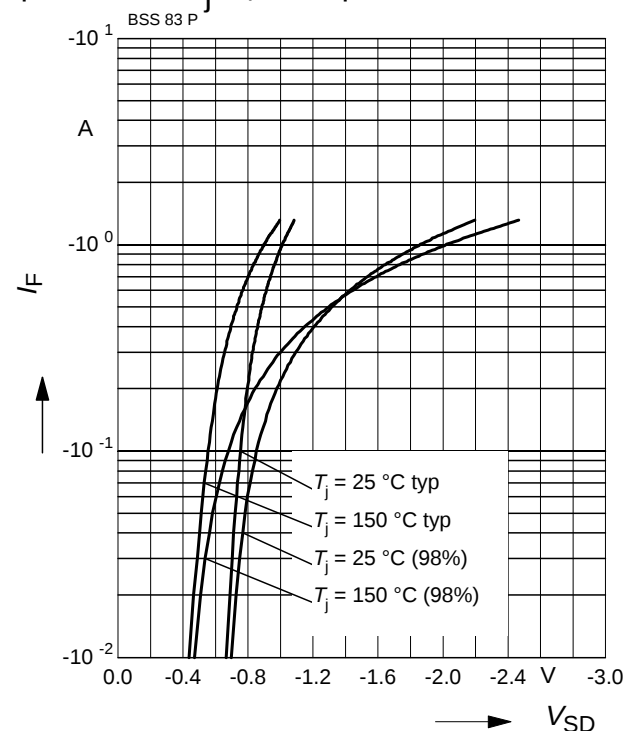
parameter: $V_{GS}=0\text{V}$, $f=1 \text{ MHz}$



Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

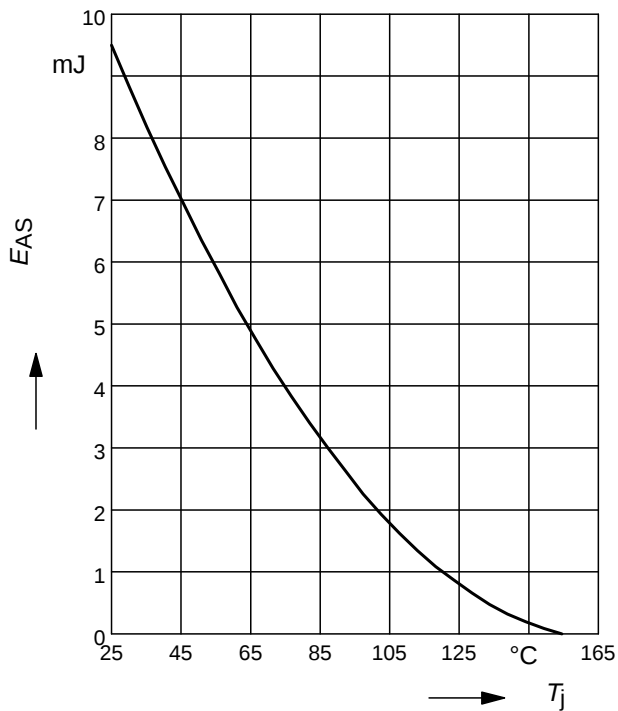
parameter: T_j , $t_p = 80 \mu\text{s}$



Avalanche energy

$$E_{AS} = f(T_j)$$

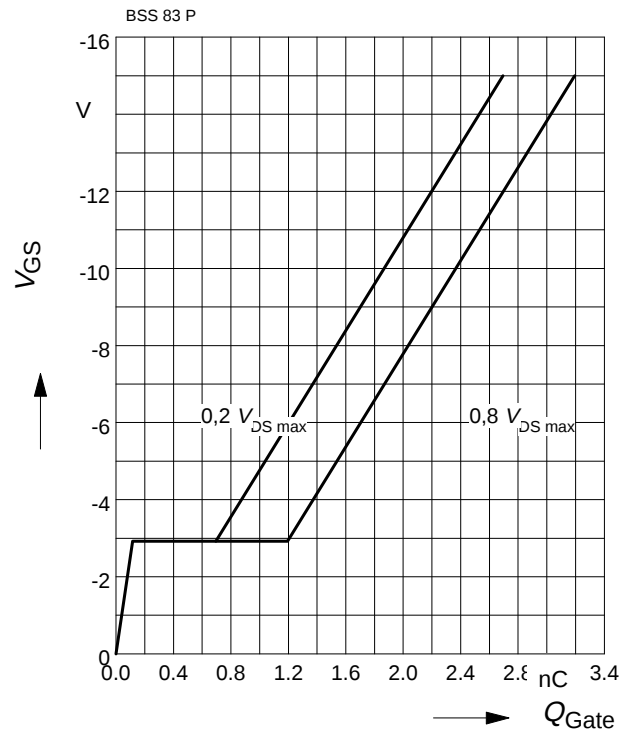
para.: $I_D = -0.33 \text{ A}$, $V_{DD} = -25 \text{ V}$, $R_{GS} = 25$



Typ. gate charge

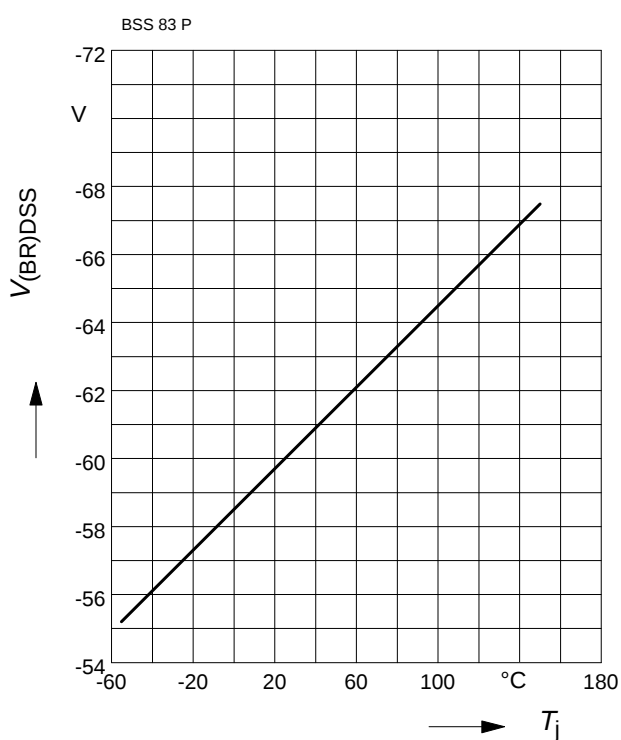
$$V_{GS} = f(Q_{Gate})$$

parameter: $I_D = -0.33 \text{ A}$ pulsed



Drain-source breakdown voltage

$$V_{(BR)DSS} = f(T_j)$$



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